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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Martin Behringer et al.

Art Unit

: Unknown

Examiner: Unknown-

Serial No.:

: Herewith

Filed Title

: SEMICONDUCTOR COMPONENT CONTAINING LATTICE MISMATCHED SEMICONDUCTOR MATERIALS

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Commissioner for Patents Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Applicant submits the references listed on the attached form PTO-1449, copies of which are enclosed. A copy of a communication from a foreign patent office in a counterpart application is also enclosed.

This statement is being filed with the application. Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: Week 1)

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Substitute Form PTO-1449
U.S. Department of Commerce (Modified)

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Information Disclosure Statement by Applicant
(Use several sheets if necessary)

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Filing Date Herewith

U.S. Patent Documents							
Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	5,396,103	03/07/1995	OIU et al.			
	AB						
	AC						
	AD						
	AE						_
	AF						
	AG	<u></u> .	-				
	AH						
	AI						

	Foreign	n Patent Doc	uments or Pu	blished Foreign	Patent A	Application	าร	
Examiner	Desig.	Document	Publication	Country or			Trans	lation
Initial	ID D	Number	Date	Patent Office	Class	Subclass	Yes	No
	AJ							
	AK							
	AL							
	AM							
	AN						·	

Other Documents (include Author, Title, Date, and Place of Publication)					
Examiner Initial	Desig. ID	Document			
	AO	Magnea, N., "ZnTe fractional monolayers and dots in a CdTe matrix" 6 th International Conference on II-VI Compounds and related optoelectric materials, Journal of Crystal Growth, 138 (1994): 550-558.			
	AP	Kutzer, V. et al., "Gain to absorption conversion by increasing excitation density in excitonic waveguides", Journal of Crystal Growth, 184/185 (1998): 632-636.			
	AQ	Faschinger, W. et al., "Processes occurring during the formation of graded ZnSe/ZnTe contacts on p-ZnSe", Semicond. Sci. Technol., 12 (1997): 1291-1297.			
	AR	Hirose, J. et al., "p-type conductivity control of ZnSe with insertion of ZnTe:Li submonolayers in metalorganic molecular-beam epitaxy", Journal of Applied Physics, 84 (01 DEC 1998): 6100-6104.			
	AS	Fan, Y. et al., "Graded band gap ohmic contact to p-ZnSe", Applied Physics Letter, 61 (26), 28 DEC 1992: 3160-3162.			

Date Considered
in conformance and not considered. Include copy of this form with
Substitute Disclosure Form (PTO-1449)